

CM4209

PNP SILICON TRANSISTOR



TO-18 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CM4209 is a PNP Saturated Switching Silicon Transistor designed for high speed switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CB0}	15	V
Collector-Emitter Voltage	V_{CE0}	15	V
Emitter-Base Voltage	V_{EBO}	4.5	V
Continuous Collector Current	I_C	200	mA
Power Dissipation	P_D	500	mW
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	1.2	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	350	$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	146	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE}=8.0\text{V}$		10	nA
I_{CES}	$V_{CE}=8.0\text{V}, T_A=125^\circ\text{C}$		5.0	μA
BV_{CB0}	$I_C=100\mu\text{A}$	15		V
BV_{CES}	$I_C=100\mu\text{A}$	15		V
BV_{CE0}	$I_C=3.0\text{mA}$	15		V
BV_{EBO}	$I_E=100\mu\text{A}$	4.5		V
$V_{CE(SAT)}$	$I_C=1.0\text{mA}, I_B=100\mu\text{A}$		0.15	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.18	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.60	V
$V_{BE(SAT)}$	$I_C=1.0\text{mA}, I_B=100\mu\text{A}$		0.80	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.69	0.86	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		1.5	V
h_{FE}	$V_{CE}=0.5\text{V}, I_C=1.0\text{mA}$	35		
h_{FE}	$V_{CE}=0.3\text{V}, I_C=10\text{mA}$	50	120	
h_{FE}	$V_{CE}=0.3\text{V}, I_C=10\text{mA}, T_A=-55^\circ\text{C}$	20		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	40		

R0 (10-June 2011)

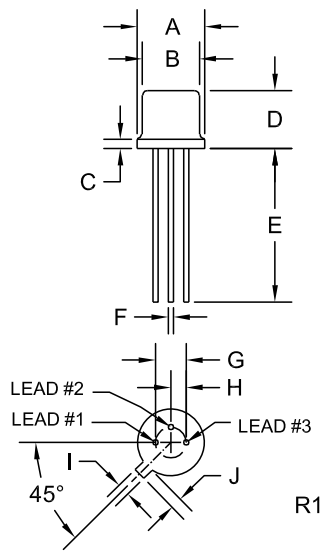
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	850		MHz
C_{ob}	$V_{CB}=5.0\text{V}$, $I_E=0$		7.0	pF
C_{ib}	$V_{BE}=0.5\text{V}$, $I_C=0$		7.0	pF
t_{on}	$V_{CC}=1.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$		20	ns
t_{off}	$V_{CC}=1.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		20	ns

TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R0 (10-June 2011)